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# **TCAD-Based Development of a Flash-EPRM Technology**

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# Contents

<b>Acknowledgements</b>	<b>i</b>
<b>Abstract</b>	<b>vii</b>
<b>Zusammenfassung</b>	<b>ix</b>
<b>1 Introduction</b>	<b>1</b>
1.1 Motivation. . . . .	.1
1.2 State-Of-The-Art Flash Technology. . . . .	2
1.3 Goal of This Work . . . . .	.3
1.4 Working Environment . . . . .	.3
1.5 Structure of This Thesis. . . . .	4
<b>2 Flash Memory Physics</b>	<b>7</b>
2.1 Flash Operation Principle. . . . .	.7
2.2 Storage Principle of Nonvolatile Memories. . . . .	.9
2.3 Programming/Erasing Mechanism for Flash EPROM Cells. . . . .	.10
2.3.1 Programming With Hot Electron Injection ..	10

2.3.2	Modeling of Hot Electron Injection. . . . .	13
2.3.3	Erasing With Fowler-Nordheim Tunneling . . . . .	14
2.3.4	Modeling of Fowler-Nordheim Tunneling . . . . .	15
<b>3</b>	<b>Flash Evaluation</b>	<b>19</b>
3.1	How to Design an Optimal Flash Cell. . . . .	19
3.2	Flash Feasibility in Standard CMOS. . . . .	22
3.3	Flash Realization in Standard CMOS. . . . .	24
3.3.1	Symmetrical Flash Cell with Boron Channel Implant . . . . .	24
3.3.2	Symmetrical Flash Cell with n-Buried Channel	24
3.3.3	Asymmetrical Flash Cell. . . . .	25
<b>4</b>	<b>Flash Technology</b>	<b>31</b>
4.1	Process Flow. . . . .	31
4.2	Gate Leakage. . . . .	36
<b>5</b>	<b>Simulation and Optimization</b>	<b>41</b>
5.1	Optimization of Symmetrical Flash Cells. . . . .	42
5.1.1	Optimization Flash Drain Implant . . . . .	44
5.1.2	Optimization of Boron Channel Implant . . . . .	48
5.1.3	Optimization of n-Buried Channel Implant . . . . .	54
5.2	vSimulation of Asymmetrical Flash Cells. . . . .	60
<b>6</b>	<b>Results Symmetrical Cells</b>	<b>65</b>
6.1	Injection and Drain Current . . . . .	66

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6.2	Breakdown Voltage. . . . .	72
6.3	Programming Performance. . . . .	75
6.4	Erasing Performance. . . . .	77
6.5	Cycling Endurance . . . . .	79
6.6	Disturb characteristics. . . . .	80
6.7	Coupling Factors and Programming Performance .	85
<b>7</b>	<b>Results Asymmetrical Cells</b>	<b>95</b>
7.1	Injection and Drain Current . . . . .	95
7.2	Programming Performance. . . . .	98
7.3	Erasing Performance. . . . .	99
<b>8</b>	<b>Design of Flash-EPROM Cells</b>	<b>101</b>
8.1	Layout Rules. . . . .	101
8.2	NOR-Memory Matrix. . . . .	103
<b>9</b>	<b>Peripheral Flash Circuits</b>	<b>107</b>
9.1	Flash Memory Design. . . . .	107
9.2	Charge Pumps. . . . .	108
9.3	High-Voltage Switches. . . . .	112
<b>10</b>	<b>Conclusions</b>	<b>117</b>
<b>A</b>	<b>List of Symbols</b>	<b>119</b>
	<b>Curriculum Vitae</b>	<b>123</b>